

General Description

The CMN2922 combines advanced trench MOSFET technology with a low resistance package to provide extremely low RDS(ON). This device is ideal for boost converters and synchronous rectifiers for consumer, telecom, industrial power supplies and LED backlighting.

Features

- RDS(ON)<120mΩ @ VGS=10V
- RDS(ON)<140mΩ @ VGS=4.5V
- SOT-23-3L Package

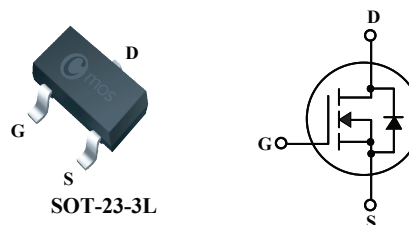
Product Summary

BVDSS	RDSON	ID
100V	120mΩ	4A

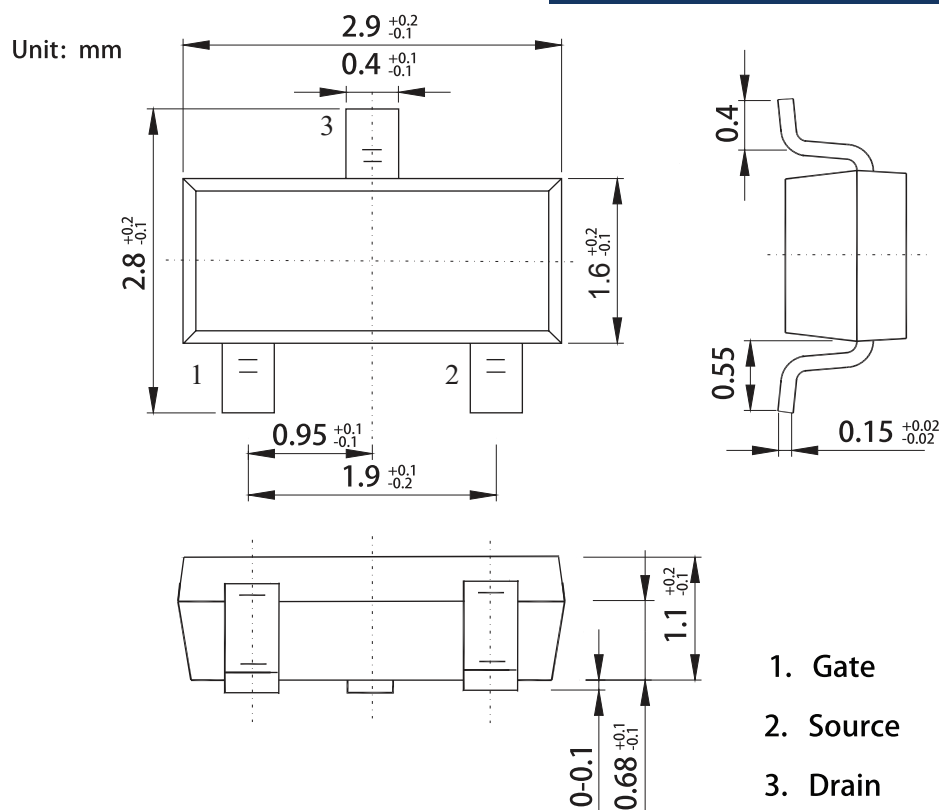
Applications

- DC-DC converters
- Load Switch
- System Switch

SOT-23-3L Pin Configuration



Type	Package	Marking
CMN2922	SOT-23-3L	2922



N-Channel Enhancement Mode Field Effect Transistor

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_{D@T_C=25^\circ C}$	Continuous Drain Current	4	A
I_{DM}	Pulsed Drain Current	16	A
$P_{D@T_A=25^\circ C}$	Total Power Dissipation	1.4	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient($t \leq 10s$)	---	90	$^\circ C/W$

Electrical Characteristics ($T_J=25^\circ C$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	100	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=2A$	---	101	120	m Ω
		$V_{GS}=4.5V, I_D=1A$	---	109	140	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1	---	3	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=100V, V_{GS}=0V$	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=3A$	---	6	---	S
Q_g	Total Gate Charge	$V_{DS}=50V, I_D=5A$ $V_{GS}=10V$	---	10	---	nC
Q_{gs}	Gate-Source Charge		---	2	---	
Q_{gd}	Gate-Drain Charge		---	3	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=50V, V_{GS}=10V, R_{GEN}=2.7\Omega$	---	5	---	ns
T_r	Rise Time		---	8	---	
$T_{d(off)}$	Turn-Off Delay Time		---	11	---	
T_f	Fall Time		---	9	---	
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, f=1MHz$	---	400	---	pF
C_{oss}	Output Capacitance		---	35	---	
C_{rss}	Reverse Transfer Capacitance		---	25	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{SD}	Diode Forward Voltage	$V_{GS}=0V, I_S=2A$	---	0.8	1.4	V

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 Cmos assumes no liability for customers' product design or applications.
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N-Channel Enhancement Mode Field Effect Transistor

Typical Characteristics

